ESCC				DOCUMENT CHANGE REQUEST		
DCR number	686 Changes required for:				Originator: Benoit Cornanguer	
Date: 2011/12/06 Date sent: 2011/10/2		2011/10/26		Organisation: STMicroelectronics		
Status: IMPLEMENTED						
Title:	TRANSISTORS, POWER, MOSFET, N-CHANNEL, RAD-HARD BASED ON TYPE STRH40N6					
Number:	5205/024 Issue:			1		
Other documents affected:						
Page:						
Pages 10 & 11						
Paragraph:						
Paragraph 2.4.	1 Room Temperatu	ure Electrical Me	easurements			
Original wordin	g:					
td(on): maximu tr: maximum lir td(off): maximu tf: minimum lim	e AC test paramete im limit=21ns instea nit=92ns instead of im limit=48ns instea nit=7ns instead of 10 nit=16ns instead of	ad of 19ns 39ns ad of 27ns Ons	off)-tf] need to b	e updated as def	ined below:	
Proposed wording:						
Justification:						
All AC electrica Unlike for the E gate charge du If we take into a	SCC qualification view to that the measu	uring the chara we have used a urements are do ent, we are sur	cterization phas test socket; in t one more far of t e to cover all cu	e have been don his case we lost p he body of the pa stomer applicatio	e near of the body of the SMD.5 package. berformance for the switching times and ackage. ns by giving to them the worst limits.	

Attachments:			
N/A			
Modifications:			
N/A			
Approval signature:			
R. C. Hari-1			
Date signed:			
2011-12-06			